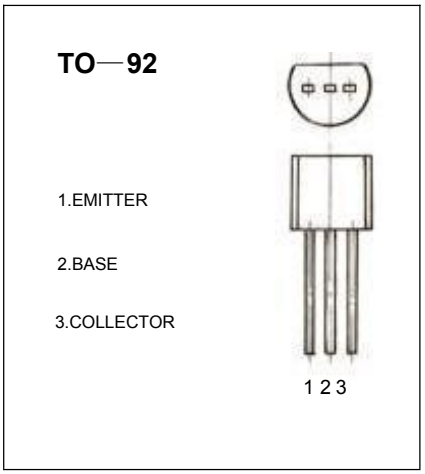
TO-92 Plastic-Encapsulate Transistors

MPSA06 TRANSISTOR（ NPN ）



FEATURES

Power dissipation

P_{CM}: 0.625 W（Tamb=25℃）

Collector current

I_{CM}: 0.5 A

Collector-base voltage

$V_{(BR)CBO}$: 80 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic=100μA, I_E=0	80			V
Collector-emitterbreakdown voltage	$V(BR)_{CEO}$	Ic=1mA, I_B=0	80			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=100μA, I_C=0	4			V
Collector cut-off current	I_{CBO}	V_{CB}= 80V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= 80V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 3V, I_C=0			0.1	μA
DC current gain(note)	H_{FE}（1）	V_{CE}=1V, I_C=10mA	100			
DC current gain(note)	H_{FE}（2）	V_{CE}=1V, I_C=100mA	100	400		
Collector-emitter saturationvoltage	V_{CE}(sat)	I_C=100mA, I_B=10mA			0.25	V
Base-emitter voltage	V_{BE}	I_B=10mA I_C=100mA			1.2	V
Transition frequency	f_T	V_{CE}=1V, I_C=10mA f=100MHz	100			MHz

CLASSIFICATION OF HFE

Rank	1	2	3
Range	100-150	150-250	250-400